Part Number	Customer

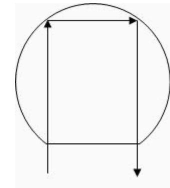
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	Customer supplied
	2.0	Primary Flat Orientation	{110}+/-0.5 degree	Customer supplied
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Customer supplied
	4.0	Secondary Flat Orientation	None	Customer supplied
	5.0	Secondary Flat Length	None	Customer supplied
	6.0	Overall Thickness	431.00 +/- 11.00 µm	ADE, 100%
	7.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	8.0	Bow	<60.00µm	ADE to ASTM F534, 20%
	9.0	Warp	<60.00µm	ADE to ASTM F657, 20%
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	5mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Customer Supplied
	13.0	Handle Orientation	{100} +/- 1.0 degree	Customer Supplied
	14.0	Handle Thickness	400.00 +/- 10.00 µm	ADE, 100%
	15.0	Handle Doping Type	Any	Customer Supplied
	16.0	Handle Dopant	Any	Customer Supplied
	17.0	Handle Resistivity	>1 Ohmcm	Customer Supplied
	18.0	Backside Finish	Polished with oxide and lasermarking	Wafer Vendor
BuriedOxide	19.0	Oxide Type	Thermal	
	20.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
	21.0	Oxide formed on	Handle and/or Device Wafer	
DeviceSilicon	22.0	Device Growth Method	CZ	Customer Supplied
	23.0	Device Orientation	{100} +/- 1.0 degree	Customer Supplied
	24.0	Nominal Thickness	30.00 +/- 0.50 µm	FTIR, 100% 9-Pt (note3)
	25.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	26.0	Device Doping Type	Any	Customer Supplied
	27.0	Device Dopant	Any	Customer Supplied
	28.0	Device Resistivity	>1 Ohmcm	Customer Supplied
	29.0	Voids	0	Bright Light, 100% (note 2)
	30.0	Scratches	0	Bright Light, 100% (note 2)
	31.0	Haze	none	Bright Light, 100% (note 2)

Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

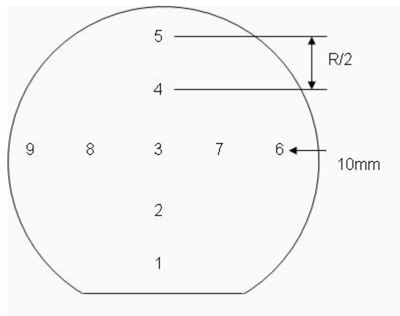
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information